**ON Semiconductor** 

Is Now

# Onsemi

To learn more about onsemi<sup>™</sup>, please visit our website at <u>www.onsemi.com</u>

onsemi and ONSEMI. and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product factures, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and asfety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or by customer's technical experts. onsemi products and actal performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use onsemi products for any such unintended or unauthorized application, Buyer shall indemnify and hold onsemi and its officers, employees, subsidiari



**ON Semiconductor®** 

# MM74HC04 Hex Inverter

#### Features

- Typical propagation delay: 8ns
- Fan out of 10 LS-TTL loads
- Quiescent power consumption: 10µW maximum at room temperature
- Low input current: 1µA maximum

### **General Description**

The MM74HC04 inverters utilize advanced silicon-gate CMOS technology to achieve operating speeds similar to LS-TTL gates with the low power consumption of standard CMOS integrated circuits.

The MM74HC04 is a triple buffered inverter. It has high noise immunity and the ability to drive 10 LS-TTL loads. The 74HC logic family is functionally as well as pin-out compatible with the standard 74LS logic family. All inputs are protected from damage due to static discharge by internal diode clamps to V<sub>CC</sub> and ground.

### **Ordering Information**

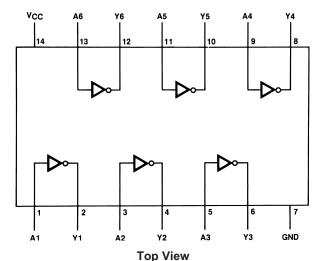
Order Number	Package Number	Package Description
MM74HC04M	M14A	14-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-012, 0.150" Narrow
MM74HC04SJ	M14D	14-Lead Small Outline Package (SOP), EIAJ TYPE II, 5.3mm Wide
MM74HC04MTC	MTC14	14-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 4.4mm Wide
MM74HC04N	N14A	14-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300" Wide

Device also available in Tape and Reel. Specify by appending suffix letter "X" to the ordering number.

All packages are lead free per JEDEC: J-STD-020B standard.

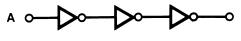
#### **Connection Diagram**

Pin Assignments for DIP, SOIC, SOP and TSSOP



Logic Diagram





### Absolute Maximum Ratings<sup>(1)</sup>

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter	Rating
V <sub>CC</sub>	Supply Voltage	–0.5 to +7.0V
V <sub>IN</sub>	DC Input Voltage	–1.5 to V <sub>CC</sub> +1.5V
V <sub>OUT</sub>	DC Output Voltage	–0.5 to V <sub>CC</sub> +0.5V
I <sub>IK</sub> , I <sub>OK</sub>	Clamp Diode Current	±20mA
I <sub>OUT</sub>	DC Output Current, per pin	±25mA
I <sub>CC</sub>	DC V <sub>CC</sub> or GND Current, per pin	±50mA
T <sub>STG</sub>	Storage Temperature Range	–65°C to +150°C
PD	Power Dissipation	
	Note 2	600mW
	S.O. Package only	500mW
ΤL	Lead Temperature (Soldering 10 seconds)	260°C

Notes:

1. Unless otherwise specified all voltages are referenced to ground.

2. Power Dissipation temperature derating — plastic "N" package: -12mW/°C from 65°C to 85°C.

#### **Recommended Operating Conditions**

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the data sheet specifications. ON Semiconductor does not recommend exceeding them or designing to absolute maximum ratings.

Symbol	Parameter	Min.	Max.	Units
V <sub>CC</sub>	Supply Voltage	2	6	V
V <sub>IN</sub> , V <sub>OUT</sub>	DC Input or Output Voltage	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature Range	-40	+85	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise or Fall Times $V_{CC} = 2.0V$		1000	ns
	$V_{CC} = 4.5V$		500	ns
	$V_{CC} = 6.0 V$		400	ns

				T <sub>A</sub> =	25°C	T <sub>A</sub> =-40°C to 85°C	T <sub>A</sub> = -55°C to 125°C	
Symbol	Parameter	$V_{CC}(V)$	Conditions	Typ. Guaranteed Limits			Limits	Units
V <sub>IH</sub>	Minimum HIGH Level	2.0			1.5	1.5	1.5	V
	Input Voltage	4.5	-		3.15	3.15	3.15	1
		6.0			4.2	4.2	4.2	1
V <sub>IL</sub>	Maximum LOW Level	2.0			0.5	0.5	0.5	V
	Input Voltage	4.5			1.35	1.35	1.35	1
		6.0			1.8	1.8	1.8	1
V <sub>OH</sub>	Minimum HIGH Level	2.0	$ V_{IN} = V_{IL},$ $ I_{OUT}  \le 20 \mu A$	2.0	1.9	1.9	1.9	V
	Output Voltage	4.5		4.5	4.4	4.4	4.4	1
		6.0		6.0	5.9	5.9	5.9	1
		4.5	$V_{IN} = V_{IL},$ $ I_{OUT}  \le 4.0 \text{mA}$	4.2	3.98	3.84	3.7	
		6.0	$V_{IN} = V_{IL},$ $ I_{OUT}  \le 5.2mA$	5.7	5.48	5.34	5.2	
V <sub>OL</sub>	Maximum LOW Level Output Voltage	2.0	$V_{IN} = V_{IH},$ $ I_{OUT}  \le 20\mu A$	0	0.1	0.1	0.1	V
		4.5		0	0.1	0.1	0.1	
		6.0		0	0.1	0.1	0.1	1
		4.5	$V_{IN} = V_{IH},$ $ I_{OUT}  \le 4.0 \text{mA}$	0.2	0.26	0.33	0.4	
		6.0	$V_{IN} = V_{IH},$ $ I_{OUT}  \le 5.2mA$	0.2	0.26	0.33	0.4	
I <sub>IN</sub>	Maximum Input Current	6.0	$V_{IN} = V_{CC}$ or GND		±0.1	±1.0	±1.0	μA
I <sub>CC</sub>	Maximum Quiescent Supply Current	6.0	$V_{IN} = V_{CC}$ or GND, $I_{OUT} = 0\mu A$		2.0	20	40	μA

#### Note:

3. For a power supply of 5V ±10% the worst case output voltages (V<sub>OH</sub>, and V<sub>OL</sub>) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V<sub>IH</sub> and V<sub>IL</sub> occur at V<sub>CC</sub> = 5.5V and 4.5V respectively. (The V<sub>IH</sub> value at 5.5V is 3.85V.) The worst case leakage current (I<sub>IN</sub>, I<sub>CC</sub>, and I<sub>OZ</sub>) occur for CMOS at the higher voltage and so the 6.0V values should be used.

## AC Electrical Characteristics

 $V_{CC} = 5V, T_A = 25^{\circ}C, C_L = 15pF, t_r = t_f = 6ns$ 

Sym	bol	Parameter	Conditions	Тур.	Guaranteed Limit	Units
t <sub>PHL</sub> , f	t <sub>PLH</sub>	Maximum Propagation Delay		8	15	ns

#### **AC Electrical Characteristics**

 $V_{CC}$  = 2.0V to 6.0V,  $C_L$  = 50pF,  $t_r$  =  $t_f$  = 6ns (unless otherwise specified)

				T <sub>A</sub> = 25°C		T <sub>A</sub> = -40°C to 85°C	T <sub>A</sub> = -55°C to 125°C	
Symbol	Parameter	V <sub>CC</sub> (V)	Conditions	Typ. Guaranteed Limits			Units	
t <sub>PHL</sub> , t <sub>PLH</sub>	Maximum	2.0		55	95	120	145	ns
	Propagation Delay	4.5		11	19	24	29	1
		6.0		9	16	20	24	1
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output	2.0		30	75	95	110	ns
	Rise and Fall Time	4.5		8	15	19	22	1
		6.0		7	13	16	19	1
C <sub>PD</sub>	Power Dissipation Capacitance <sup>(4)</sup>		(per gate)	20				pF
C <sub>IN</sub>	Maximum Input Capacitance			5	10	10	10	pF

#### Note:

4.  $C_{PD}$  determines the no load dynamic power consumption,  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ , and the no load dynamic current consumption,  $I_S = C_{PD} V_{CC} f + I_{CC}$ .